

WHAT IS CLAIMED IS:

1. A method for manufacturing semiconductor material comprising the steps of:

5 introducing a metal element into a region of an amorphous semiconductor film, the metal element accelerating crystallization of the semiconductor film;

crystallizing at least part of the semiconductor film by forming a temperature gradient in the semiconductor film and causing

10 crystal growth from the region where the metal element is introduced to another region of the semiconductor film by utilizing the temperature gradient.